

1. Record Nr.	UNINA9910464348003321
Autore	Chan-Lau Jorge A
Titolo	The credit risk transfer market and stability implications for U.K. financial institutions [[electronic resource] /] / Jorge A. Chan-Lau and Li Lian Ong
Pubbl/distr/stampa	[Washington, D.C.], : International Monetary Fund, Monetary and Financial Systems Dept., 2006
ISBN	1-4623-3971-9 1-4527-3299-X 1-283-51751-5 9786613829962 1-4519-0918-7
Descrizione fisica	1 online resource (27 p.)
Collana	IMF working paper ; ; WP/06/139
Altri autori (Persone)	OngLi Lian
Soggetti	Credit derivatives - Great Britain Derivative securities - Great Britain Electronic books.
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2. Record Nr.	UNINA9910143584503321
Autore	Gutierrez Inigo
Titolo	Design and characterization of integrated varactors for RF applications [[electronic resource] /] / Inigo Gutierrez, Juan Melendez, Erik Hernandez
Pubbl/distr/stampa	Chichester, West Sussex, England ; ; Hoboken, NJ, : Wiley, c2006
ISBN	1-280-85476-6 9786610854769 0-470-03592-7 1-60119-377-7 0-470-03591-9
Descrizione fisica	1 online resource (182 p.)
Altri autori (Persone)	MelendezJuan <1974-> HernandezErik
Disciplina	621.3815 621.381522
Soggetti	Varactors - Design and construction Radio capacitors - Design and construction Radio circuits - Design and construction Integrated circuits - Design and construction Electronic books.
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Nota di contenuto	Design and Characterization of Integrated Varactors for RF Applications; Contents; List of Figures; List of Tables; Preface; Acknowledgements; 1 Introduction; 1.1 Passive Elements; 1.2 Figures of Merit of Varactors; 1.2.1 Quality Factor; 1.2.2 Tuning Range; 1.2.3 Self-resonant Frequency(fR); 1.2.4 Effective Silicon Area; 1.2.5 Absolute Capacity Value; 1.3 Principal Types of Varactor Manufacture; 1.3.1 Discrete Varactors; 1.3.2 MEMS Varactors; 1.3.3 BST Varactors; 1.3.4 Integrated Varactors using Standard Technologies; References; 2 PN-junction Varactors 2.1 The Operating Principle of a PN-junction Varactor2.1.1 Electrical Phenomena in a PN-junction Varactor; 2.2 Different Architectures of

PN-junction Varactors; 2.2.1 Different Configurations of PN-junction Varactors; 2.3 Influence of Bias Voltage on the Behaviour of a PN-junction Varactor; 2.4 Influence of Geometric Parameters on the Behaviour of a PN-junction Varactor; 2.4.1 Influence in the Variation of the Number of Islands; 2.4.2 Influence of the Size of the Islands; 2.4.3 Influence of the Distance Between Islands; 2.4.4 Variation of the Size of the N Well
2.5 Influence of the Working Frequency on the Results
2.5.1 Influence of the Frequency on the Quality of a Varactor; 2.5.2 Influence of the Frequency on the Capacitance of a Varactor; 2.6 Comparison Between the Different Types of PN-junction Varactors; 2.6.1 Comparison According to the Effective Silicon Area; 2.6.2 Comparison According to the Quality Factor; References; 3 MOS Varactors; 3.1 Operating Principles of an NMOS Varactor; 3.1.1 Operating Ranges of the NMOS Varactor; 3.1.2 Electrical Phenomena of an NMOS Varactor in Accumulation Mode
3.1.3 Electrical Phenomena of an NMOS Varactor in Depletion Mode
3.2 NMOS Varactors; 3.2.1 Operating Ranges of the NMOS Varactor; 3.3 Influence of the Operating Mode on an NMOS Varactor; 3.4 Influence of Bias Voltage on the Behaviour of an NMOS Accumulation Varactor; 3.5 Influence of Geometric Parameters on the Behaviour of an NMOS Varactor; 3.5.1 Influence of the Variation of the Varactor Size; 3.5.2 Influence of the Varactor Gate Length on its Performance; 3.5.3 Influence of the Varactor Gate Width on its Performance; 3.6 Influence of the Working Frequency on the Results; References
4 Measurement Techniques for Integrated Varactors
4.1 Test System; 4.2 Equipment Required for the On-Wafer Testing of Integrated Varactors; 4.2.1 Test Probes; 4.2.2 Connectivity; 4.3 Calibrating the Test System; 4.4 Test Structures; 4.4.1 Choosing the Test Structure Configuration; 4.4.2 Design of the Test Structures; 4.4.3 Effects Introduced by the Test Structures; 4.5 Test Structure DE-embedding Techniques; 4.5.1 Single-Short Structure; 4.5.2 Single-Open Structure; 4.5.3 Thru Structure; 4.6 Characterization of Integrated Varactors; 4.7 Test System Verification
4.7.1 Error Introduced by Positioning the Test Probes on the Pads

Sommario/riassunto

Varactors are passive semiconductor devices used in electronic circuits, as a voltage-controlled way of storing energy in order to boost the amount of electric charge produced. In the past, the use of low-cost fabrication processes such as complementary metal oxide semiconductor (CMOS) and silicon germanium (SiGe) were kept for integrated circuits working in frequency ranges below the GHz. Now, the increased working frequency of radio frequency integrated circuits (RF ICs) for communication devices, and the trend of system-on-chip technology, has pushed the requirements of varactors to the lim

3.	Record Nr.	UNIORUON00507624
	Autore	Auslander, Philip
	Titolo	From acting to performance : essays in modernism and postmodernism / Philip Auslander
	Pubbl/distr/stampa	London, : Routledge, : Taylor & Francis, 1997
	ISBN	978-02-03-44426-9
	Descrizione fisica	1 risorsa online (X, 173 p.)
	Disciplina	792.028
	Soggetti	Recitazione - Tecnica
	Lingua di pubblicazione	Inglese
	Formato	Risorsa elettronica
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4.	Record Nr.	UNINA9910482496603321
	Autore	Hippocrates
	Titolo	Aphorismorum sectiones octo; ex interpretatione Anutii Foesii. Quibus accessit methodus, qua aphorismi, in certum ordinem digesti, & accurate dispositi / exhibentur a Joanne Ernesto Scheffler .
	Pubbl/distr/stampa	Leiden, : Joannes Maire, 1633
	Descrizione fisica	Online resource ([8], 280 p. , (32mo))
	Altri autori (Persone)	FoesAnuce <1528-1595.> SchefflerJoannes Ernestus
	Lingua di pubblicazione	Greco antico
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